a plurality of memory cells, for storing data, each cell having at least a transfer MOS transistor;

a plurality of word lines, each word line coupled with gate electrodes of said transfer MOS transistors of said plurality of memory cells;

a word driver circuit for providing an output voltage to a word line of said plurality of word lines; and

a voltage generator circuit supplied with an operating voltage so as to provide a first voltage to said word driver circuit;

wherein the amplitude of said first voltage is larger than that of said operating voltage so that said word driver circuit can provide the output voltage whose amplitude is larger than an amplitude of an input voltage;

wherein said voltage generator circuit provides a small output current to said word driver circuit in order to [compensate for a leakage current] keep the output voltage thereof to the first voltage and [said voltage generator circuit] provides a large output current to said word driver circuit in response to a first signal from an outside chip.

Claim 22 (Amended)

The semiconductor memory according to claim 21, wherein said voltage generator circuit includes:

a first circuit supplied with an operating voltage so as to provide a first voltage to said word driver circuit; and

a second circuit supplied with the operating voltage so as to provide the

first voltage to said word driver circuit;

wherein said first circuit provides the first voltage in response to [a] the first signal from the outside chip;

wherein said second circuit provides [the first voltage] said small output current to said word driver circuit in order to [compensate for a leakage current] keep the output voltage of said voltage generator circuit to the first voltage while said first circuit stops providing the first voltage to said word driver circuit.

Claim ~~24~~ 4 (Amended)

The semiconductor memory according to claim [23] ~~22~~ 2, wherein said second circuit has a detector circuit which provides a signal to make said second circuit stop providing said first voltage when the first voltage is larger than the predetermined voltage.

Please add new claim 28 as follows.

Claim 28 (New)

The semiconductor memory according to claim 21, wherein said voltage generator circuit has a rectifier at the output.

## REMARKS

The specification was amended by Preliminary Amendment filed with the application on September 13, 1994 and new claims 21-27 were added. Claims 21, 22 and 24 have been amended and new claim 28 has been added as set forth above.